



GSX30160T

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

Trench MOSFET

30V N-Chanel Power Transistor

GSX30160T

Data Sheet

Ver 0

2023-2-5

30V 160A Power MOSFET

■ Description

GroupSemi (GS) has series Trench power MOSFET platforms for voltage up 20V to 200 volts, both with design service and manufacturing capability, including cell, termination design and simulation.

The GS 30V 160A power MOSFET is a Low voltage N channel Trench power MOSFET sample with advanced technology to have better characteristics, such as fast switching time, low Ciss and Crss, low on resistance and excellent avalanche characteristics, making it especially suitable for applications which require superior power density and outstanding efficiency.

■ Features

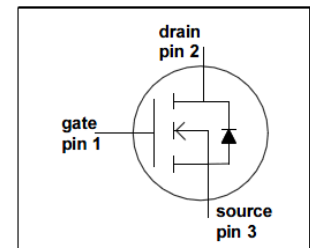
$R_{DS(ON)} < 1.7m\ \Omega$ @ $V_{GS} = 10V$

$V_{DS} = 30V$

I_D (@ $V_{GS}=10V$) = 20A

■ PKG

GSS30160T	GSD30160T	GSA30160T	GSP30160T	GSB30160T
TO-251	TO-252	TO-220Fullpak	TO-220	TO-263



■ Absolute Maximum Ratings (TC = 25° C, unless otherwise specified)

Symbol	Parameter	Maximum	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D^{(1)}$	Continuous Drain Current (TC=25° C)	210	A
	Continuous Drain Current (TC=100° C)	160	
$I_{DM}^{(2)}$	Pulsed Drain Current	450	A

30V 160A Power MOSFET

EAR ^{(2),(3)}	Repetitive avalanche energy	35	mJ
EAS ⁽⁴⁾	Single pulsed avalanche energy (1mH)	123	mJ
dv/dt	Peak diode recovery dv/dt	5	V/ns
PD ⁽¹⁾	Power Dissipation (TC=25° C) TO-220	118	W
	Derating above 25° C	1.5	W/ ° C
TJ	Max. operating junction temperature	150	° C
TSTG	Storage temperature	-55 to +150	° C

■ Thermal Characteristics

Symbol	Parameter	Value (TO220)	Unit
R _{θJA} ⁽⁶⁾	Maximum Junction-to-Ambient	82	C/W
R _{θCS} ⁽⁶⁾	Maximum Case-to-sink	0.6	C/W
R _{θJC} ^{(7),(8)}	Maximum Junction-to-Case θ	4.1	C/W

1. The power dissipation PD is based on TJ(MAX)=150° C in a TO-251 package, using junction-to-case thermal resistance.
2. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150° C.
3. L=1mH, Starting TJ=25° C.
4. L = 10mH, starting TJ = 25° C.
5. L=60mH, starting TJ = 25° C.
6. The tests are performed with the device with T A =25° C.
7. The R _{θJA} is the sum of the thermal impedance from junction to case R _{θJC} and case to ambient.
8. These curves are based on the junction-to-case thermal impedance, assuming a maximum junction temperature of TJ(MAX)=150° C.

30V 160A Power MOSFET

■ Electrical Characteristics (T_J=25° C unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Off Characteristics						
BVDSS	Drain-Source Breakdown Voltage	ID=250uA, VGS=0V, T _J =25° C	30	32		V
BVDSS /ΔT _J	Zero Gate Voltage Drain Current	ID=250uA, VGS=0V		0.72		V/° C
IDSS	Zero Gate Voltage Drain Current	VDS=30V, VGS=0V			1	uA
		VDS=30V, T _J =125° C	10			
IGSS	Gate-Body leakage current	VDS=0V, VGS=20V			100	nA
		VDS=0V, VGS=-20V	-100			
On Characteristics						
VGS(th)	Gate Threshold Voltage	VDS=Vgs, ID=250uA	1.1	1.7	2.3	V
RDS(ON)	Static Drain-Source On-Resistance	VGS=10V, ID=20A		1.4	1.7	mΩ
gFS	Forward Transconductance	VDS = 5 V, ID = 20A		85		S
Source Drain Diode Characteristics						
VSD	Diode Forward Voltage	IS=1A, VGS=0V		0.82	1.2	V
ISD	Continuous source-drain Current			50		A
trr	Reverse Recovery Time	IF=20A, dI/dt=100A/us		18		ns
Qrr	Reverse Recovery Charge	IF=20A, dI/dt=100A/us		37		nC
Dynamic Characteristics						
Ciss	Input Capacitance	VGS=0V, VDS=15V, f=1MHz		2800		pF
Coss	Output Capacitance	VGS=0V, VDS=15V, f=1MHz		1000		pF
Crss	Reverse Transfer Capacitance	VGS=0V, VDS=15V, f=1MHz		80		pF
Qg	Total Gate Charge	VDS=10V, ID=20A		37		nC
Qgs	Gate Source Charge	VDS=10V, ID=20A		7.4		nC
Qgd	Gate Drain Charge	VDS=10V, ID=20A		3.6		nC
Switching Characteristics						
t _d (on)	Turn-On DelayTime	VGS=10V, VDS=15V, ID=15A, RG=2.5 Ω		7.5		ns
tr	Turn-On Rise Time			5		ns
t _d (off)	Turn-Off DelayTime			60		ns
tf	Turn-Off Fall Time			16		ns

30V 160A Power MOSFET

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

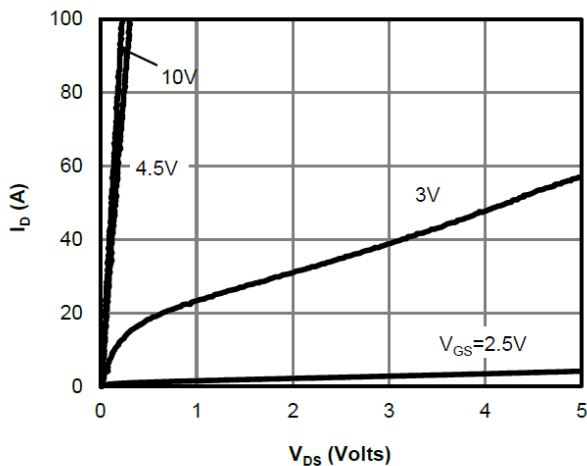


Figure 1: On-Region Characteristics (Note E)

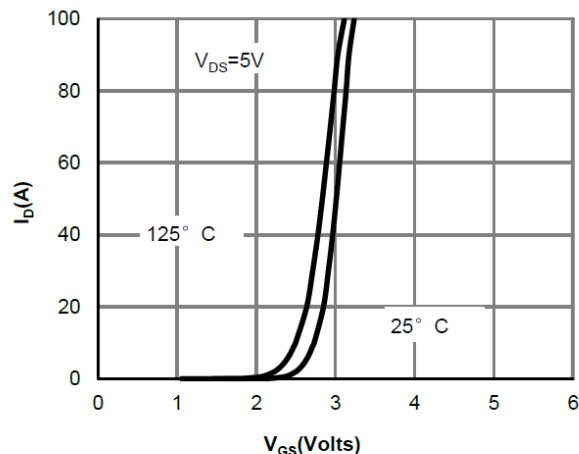


Figure 2: Transfer Characteristics (Note E)

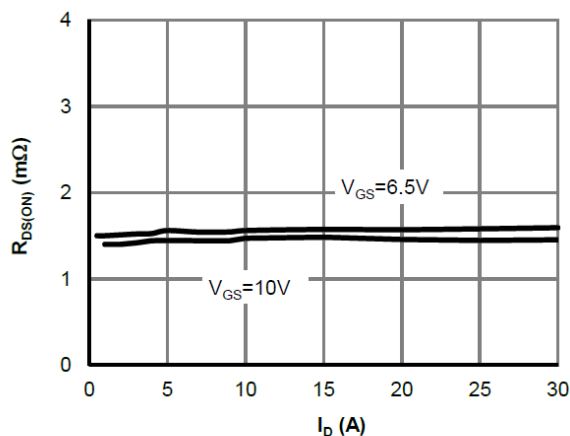


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

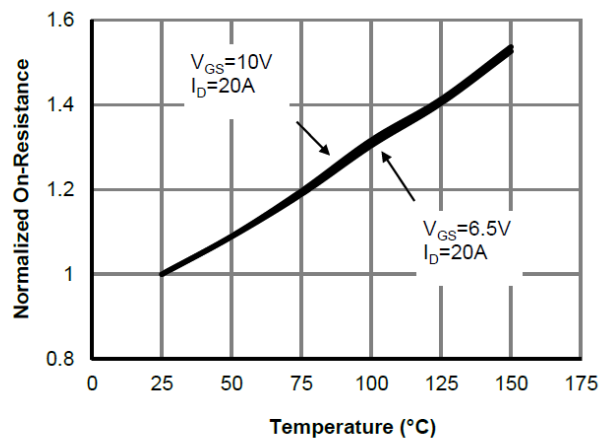


Figure 4: On-Resistance vs. Junction Temperature (Note E)

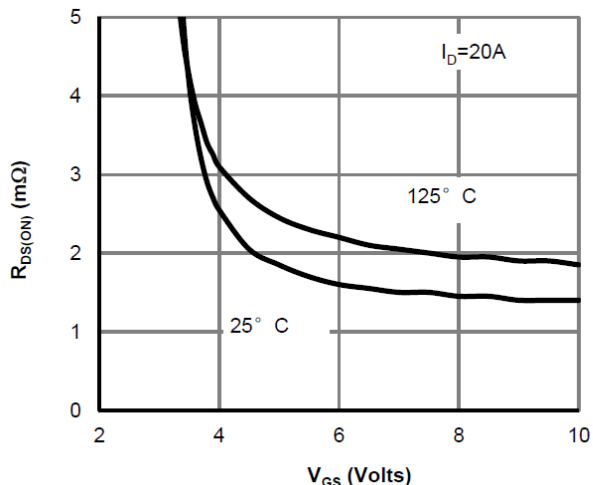


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

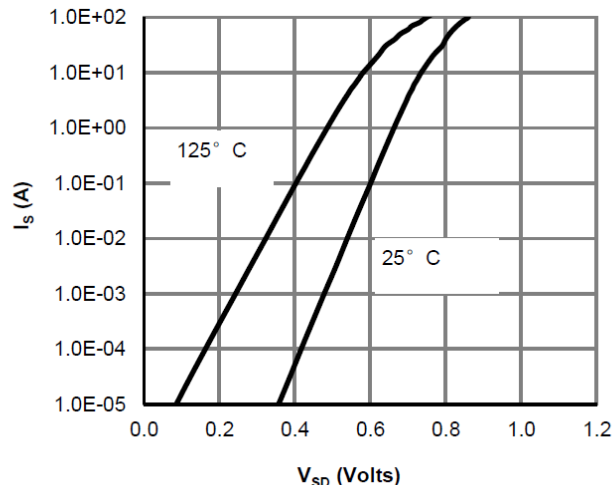


Figure 6: Body-Diode Characteristics (Note E)

30V 160A Power MOSFET

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

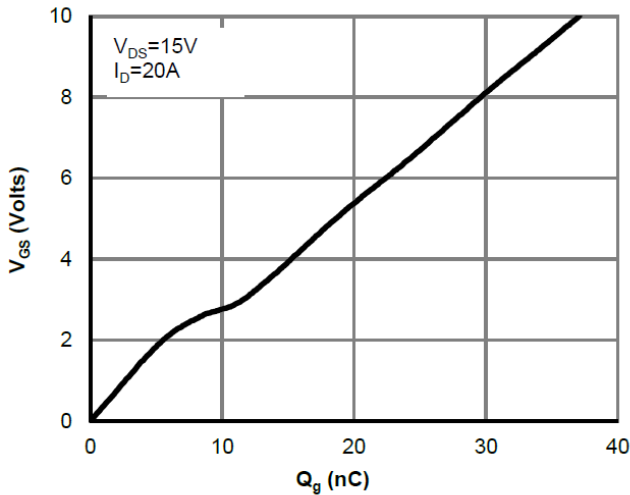


Figure 7: Gate-Charge Characteristics

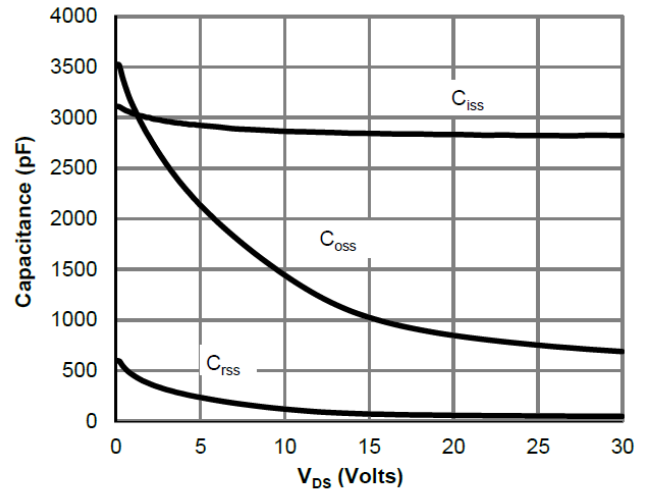


Figure 8: Capacitance Characteristics

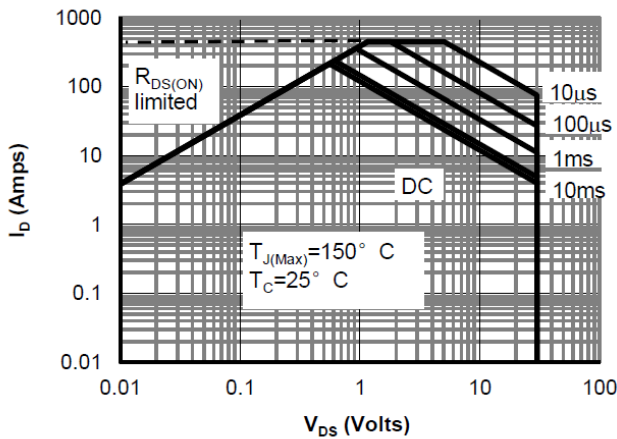


Figure 9: Maximum Forward Biased

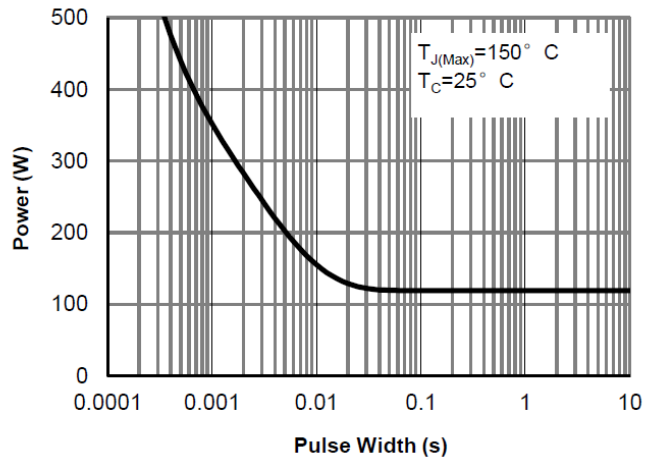


Figure 10: Single Pulse Power Rating Junction-to-Case

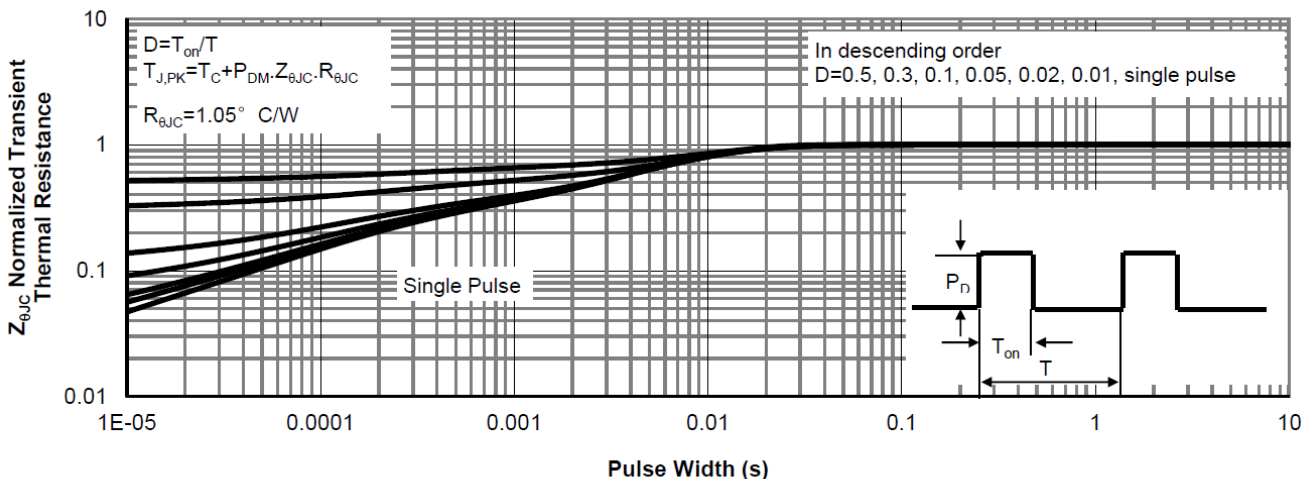


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

30V 160A Power MOSFET

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

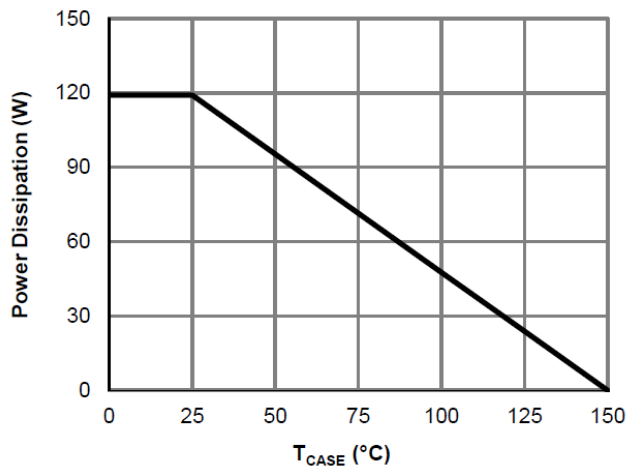


Figure 12: Power De-rating (Note F)

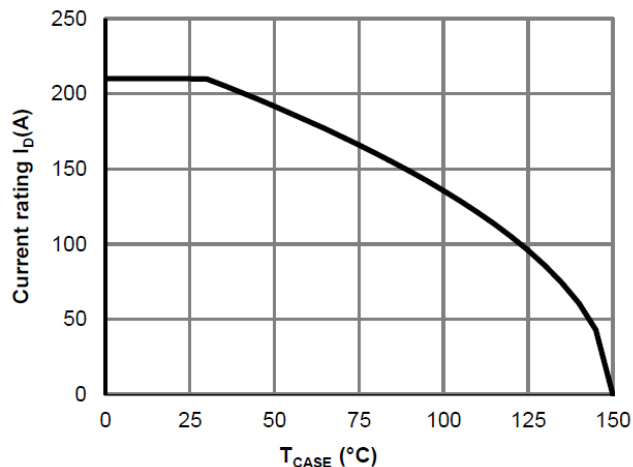


Figure 13: Current De-rating (Note F)

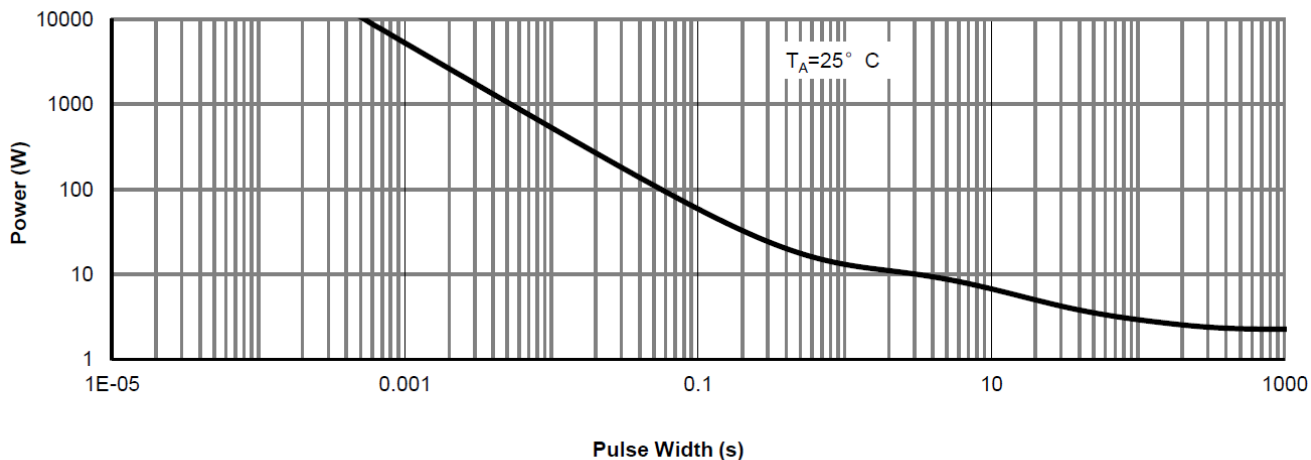


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note G)

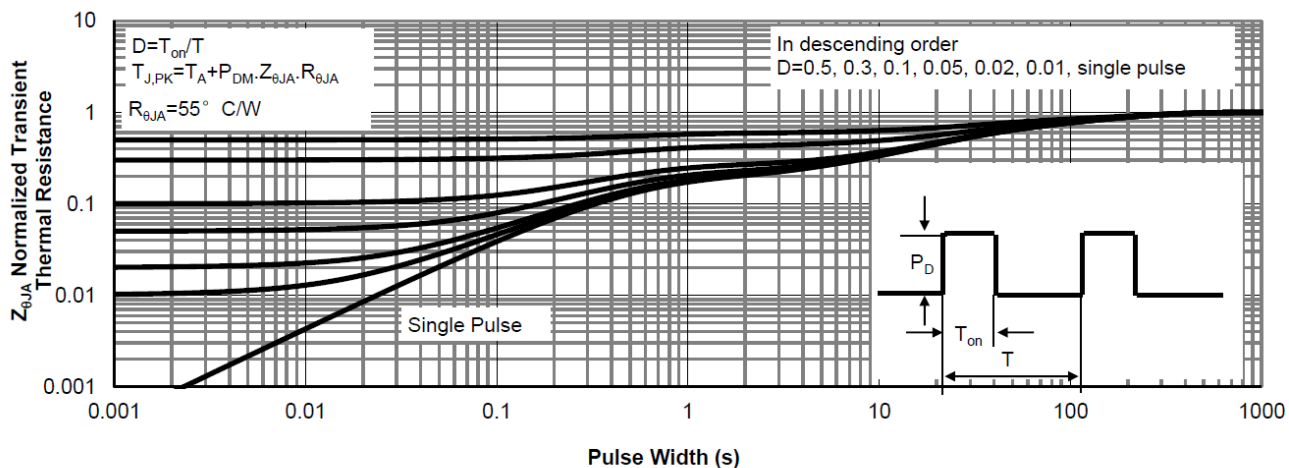


Figure 15: Normalized Maximum Transient Thermal Impedance (Note G)

30V 160A Power MOSFET

Table 20 Switching times test circuit and waveform for inductive load

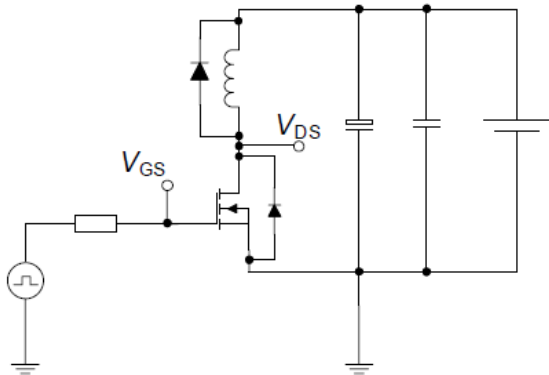
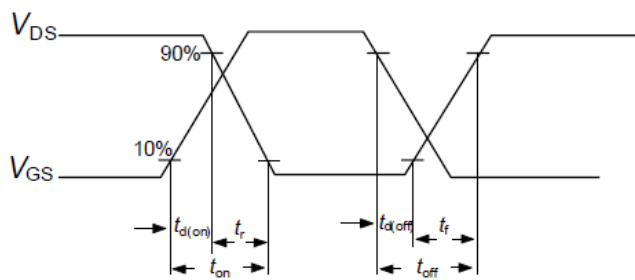
Switching times test circuit for inductive load	Switching time waveform
	

Table 21 Unclamped inductive load test circuit and waveform

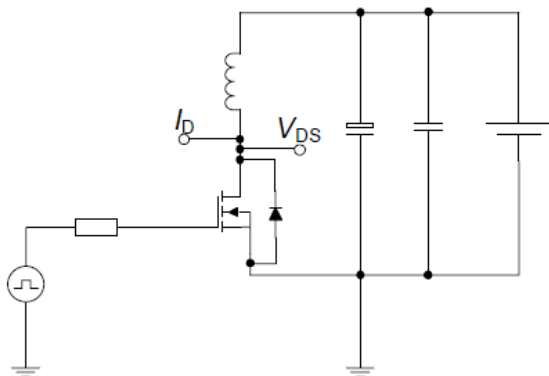
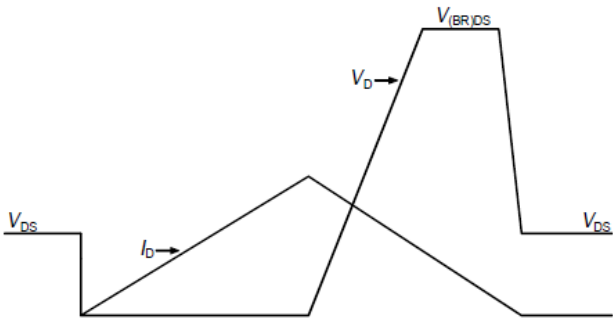
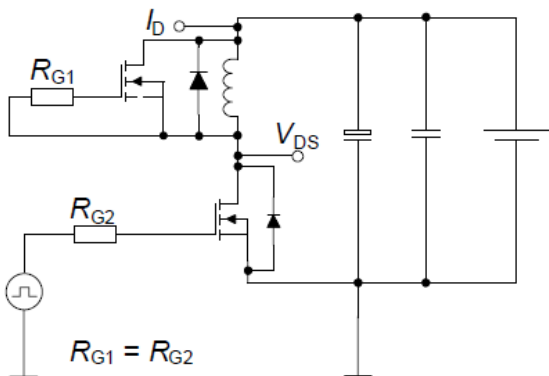
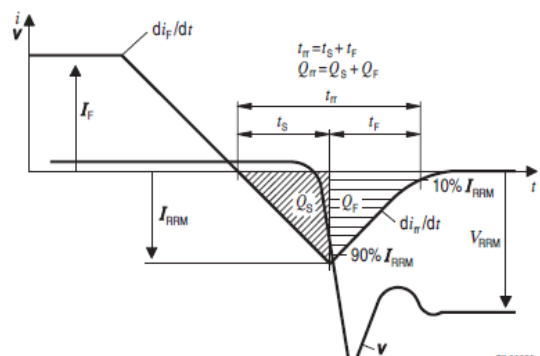
Unclamped inductive load test circuit	Unclamped inductive waveform
	

Table 22 Test circuit and waveform for diode characteristics

Test circuit for diode characteristics	Diode recovery waveform
 $R_{G1} = R_{G2}$	 $t_{tr} = t_s + t_r$ $Q_{rr} = Q_s + Q_F$